Lattice Semiconductor Corporation - LCMXO3L-4300E-5MG324C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

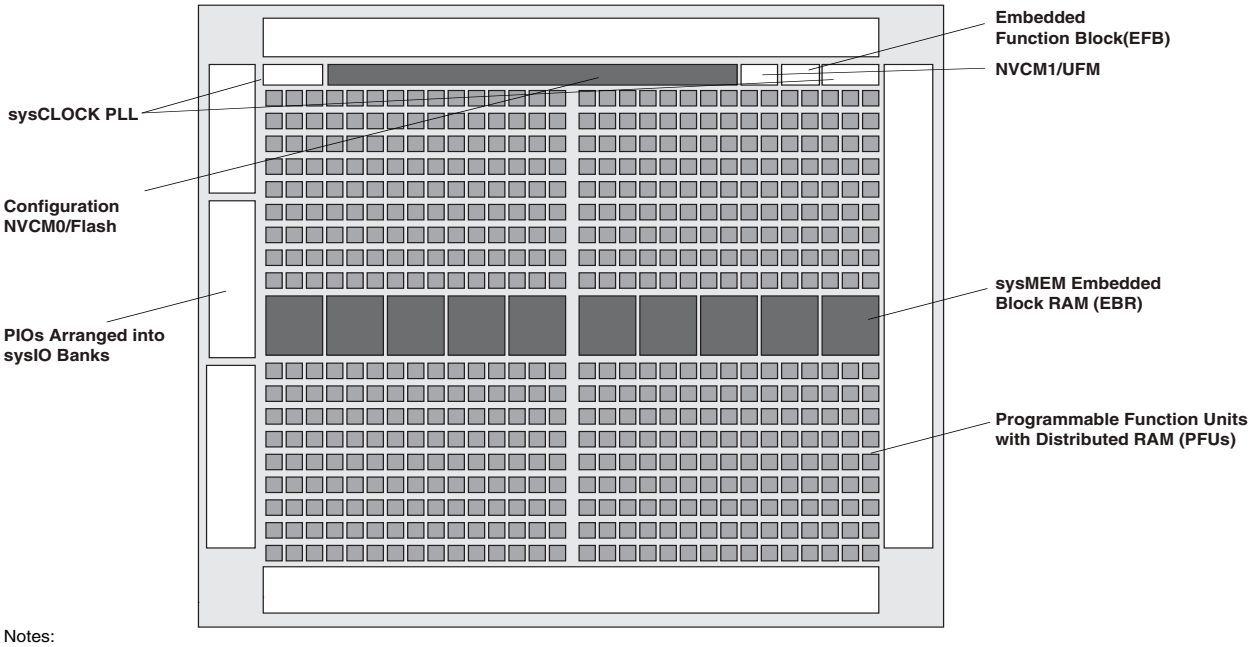
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	268
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	324-VFBGA
Supplier Device Package	324-CSFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3l-4300e-5mg324c

Figure 2-2. Top View of the MachXO3L/LF-4300 Device



Notes:
- MachXO3L/LF-1300, MachXO3L/LF-2100, MachXO3L/LF-6900 and MachXO3L/LF-9400 are similar to MachXO3L/LF-4300. MachXO3L/LF-1300 has a lower LUT count, one PLL, and seven EBR blocks. MachXO3L/LF-2100 has a lower LUT count, one PLL, and eight EBR blocks. MachXO3L/LF-6900 has a higher LUT count, two PLLs, and 26 EBR blocks. MachXO3L/LF-9400 has a higher LUT count, two PLLs, and 48 EBR blocks.
- MachXO3L devices have NVCM, MachXO3LF devices have Flash.

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO3L/LF family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag “hard” control logic to minimize LUT usage.

The MachXO3L/LF registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO3L/LF architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. These blocks are located at the ends of the on-chip NVCM/Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO3L/LF devices provide commonly used hardened functions such as SPI controller, I^2C controller and timer/counter.

MachXO3LF devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I^2C and JTAG ports.

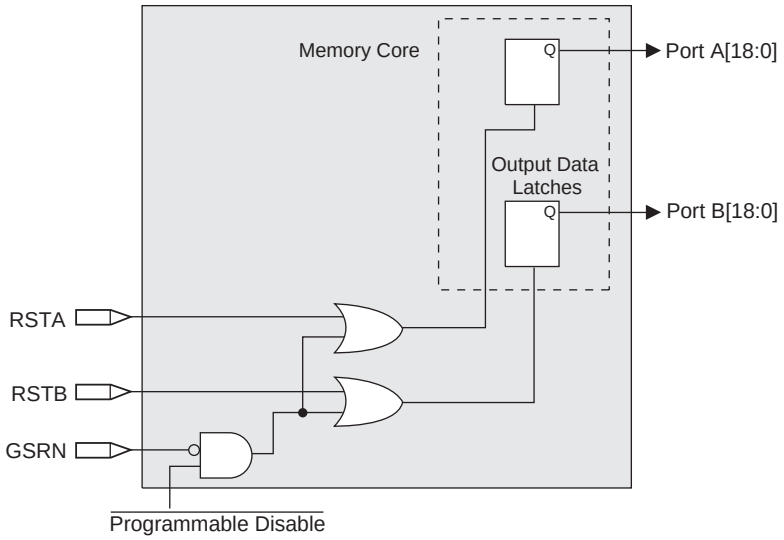
Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO3L/LF devices are available for operation from 3.3 V, 2.5 V and 1.2 V power sup-plies, providing easy integration into the overall system.

state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

Figure 2-9. Memory Core Reset

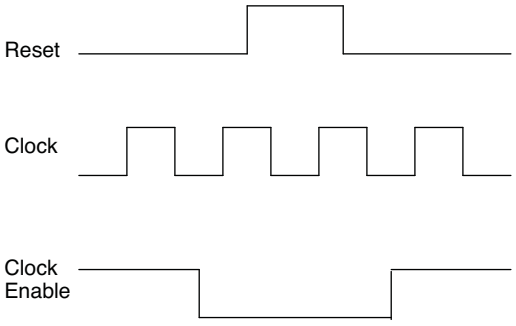


For further information on the sysMEM EBR block, please refer to TN1290, Memory Usage Guide for MachXO3 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

Input Gearbox

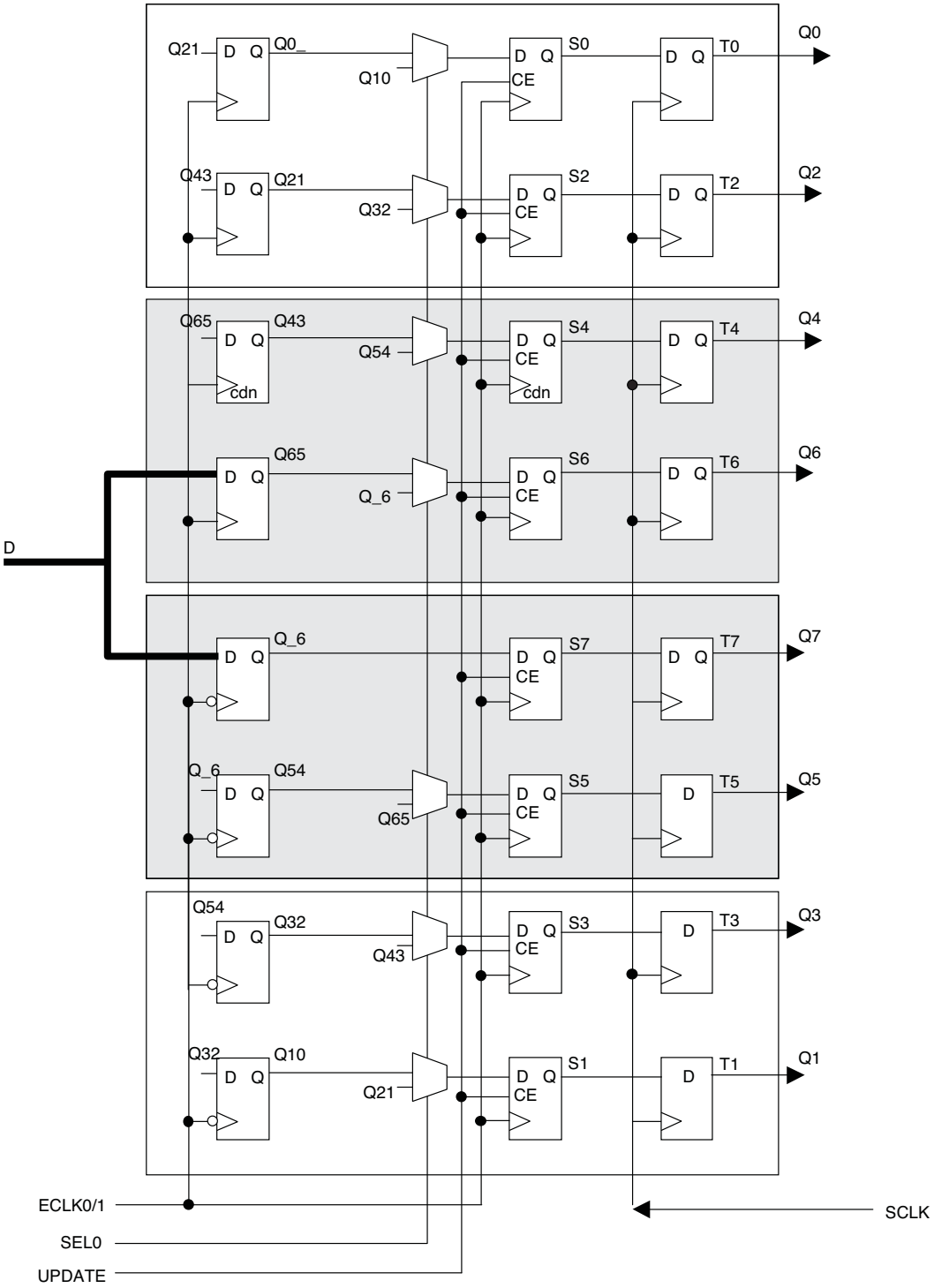
Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Table 2-9. Input Gearbox Signal List

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDRX4(1:8): Q[7:0] GDDRX2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDRX2(1:4)(IOL-C): Q0, Q1, Q2, Q3

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-13 shows a block diagram of the input gearbox.

Figure 2-13. Input Gearbox



More information on the input gearbox is available in TN1281, Implementing High-Speed Interfaces with MachXO3 Devices.

Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDRX4 (8:1) gearbox or as two ODDRX2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDRX4(8:1): D[7:0]		
GDDRX2(4:1)(IOL-A): D[3:0]		
GDDRX2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-14 shows the output gearbox block diagram.

Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, MachXO3 sysIO Usage Guide.

Table 2-11. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3 V**	**2.5 V**	**1.8 V**	**1.5 V**	**1.2 V**
Single-Ended Interfaces					
LVTTL	Yes				
LVCMOS33	Yes				
LVCMOS25		Yes			
LVCMOS18			Yes		
LVCMOS15				Yes	
LVCMOS12					Yes
PCI	Yes				
Differential Interfaces					
LVDS	Yes	Yes			
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes			
MIPI[1]	Yes	Yes			
LVTTLD	Yes				
LVCMOS33D	Yes				
LVCMOS25D		Yes			
LVCMOS18D			Yes		

1. These interfaces can be emulated with external resistors in all devices.

Hardened Timer/Counter

MachXO3L/LF devices provide a hard Timer/Counter IP core. This Timer/Counter is a general purpose, bi-directional, 16-bit timer/counter module with independent output compare units and PWM support. The Timer/Counter supports the following functions:

- Supports the following modes of operation:
  — Watchdog timer
  — Clear timer on compare match
  — Fast PWM
  — Phase and Frequency Correct PWM
- Programmable clock input source
- Programmable input clock prescaler
- One static interrupt output to routing
- One wake-up interrupt to on-chip standby mode controller.
- Three independent interrupt sources: overflow, output compare match, and input capture
- Auto reload
- Time-stamping support on the input capture unit
- Waveform generation on the output
- Glitch-free PWM waveform generation with variable PWM period
- Internal WISHBONE bus access to the control and status registers
- Stand-alone mode with preloaded control registers and direct reset input

Figure 2-20. Timer/Counter Block Diagram

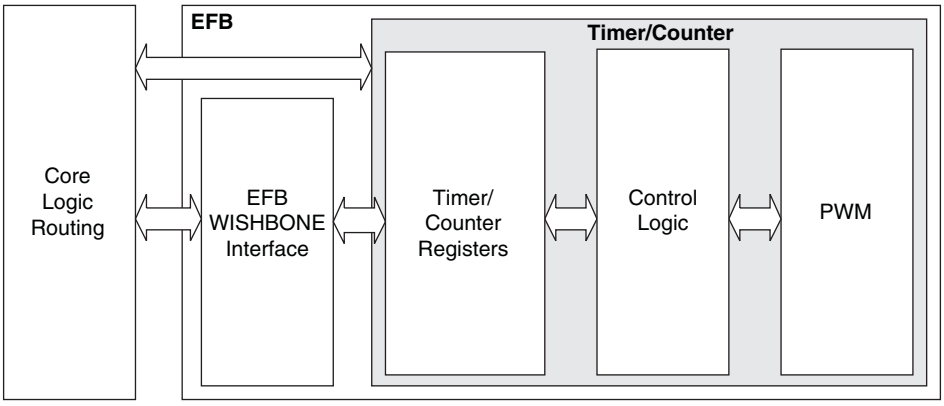


Table 2-16. Timer/Counter Signal Description

Port	I/O	Description
tc_clki	I	Timer/Counter input clock signal
tc_rstn	I	Register tc_rstn_ena is preloaded by configuration to always keep this pin enabled
tc_ic	I	Input capture trigger event, applicable for non-pwm modes with WISHBONE interface. If enabled, a rising edge of this signal will be detected and synchronized to capture tc_cnt value into tc_icr for time-stamping.
tc_int	O	Without WISHBONE – Can be used as overflow flag With WISHBONE – Controlled by three IRQ registers
tc_oc	O	Timer counter output signal

For more details on these embedded functions, please refer to TN1293, Using Hardened Control Functions in MachXO3 Devices.

User Flash Memory (UFM)

MachXO3LF devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1293, Using Hardened Control Functions in MachXO3 Devices.

Standby Mode and Power Saving Options

MachXO3L/LF devices are available in two options, the C and E devices. The C devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the E devices operate at 1.2 V V_{CC}.

MachXO3L/LF devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO3L/LF devices support a low power Stand-by mode.

In the stand-by mode the MachXO3L/LF devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I^2C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO3L/LF devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Table 2-17. MachXO3L/LF Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Differential I/O buffers (used to implement standards such as LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1289, Power Estimation and Management for MachXO3 Devices.

Power On Reset

MachXO3L/LF devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration NVCM/Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For “E” devices without voltage regulators, V_{CCINT} is the same as the V_{CC} supply voltage. For “C” devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as NVCM/Flash Download Time ($t_{REFRESH}$) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for “C” devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once an “E” device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a mini-mal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} - 0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} - 0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < $V_{IN} < V_{CCIO}$	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	–309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < $V_{IN} < V_{CCIO}$	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pf
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For true LVDS output pins in MachXO3L/LF devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1280, MachXO3 sysIO Usage Guide.

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of the MachXO3L/LF PLD family.

LVDS

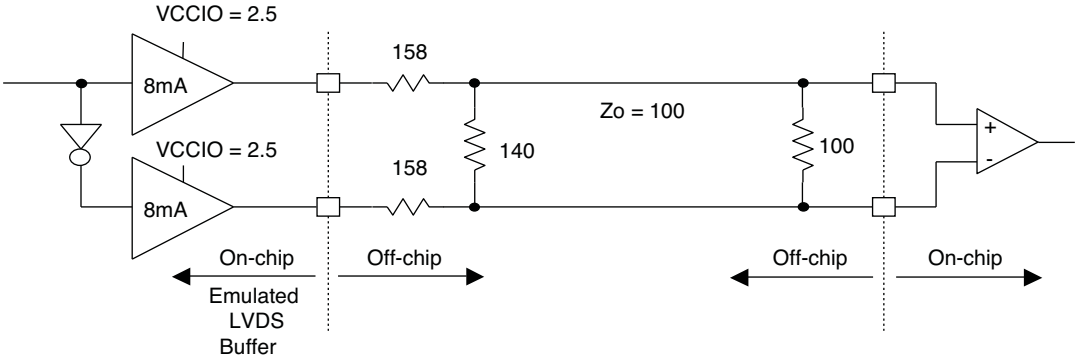
Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP}, V_{INM}	Input Voltage	V_{CCIO} = 3.3 V	0	—	2.605	V
		V_{CCIO} = 2.5 V	0	—	2.05	V
V_{THD}	Differential Input Threshold		±100	—		mV
V_{CM}	Input Common Mode Voltage	V_{CCIO} = 3.3 V	0.05	—	2.6	V
		V_{CCIO} = 2.5 V	0.05	—	2.0	V
I_{IN}	Input current	Power on	—	—	±10	µA
V_{OH}	Output high voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	—	1.375	—	V
V_{OL}	Output low voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	0.90	1.025	—	V
V_{OD}	Output voltage differential	(V_{OP} - V_{OM}), R_T = 100 Ohm	250	350	450	mV
ΔV_{OD}	Change in V_{OD} between high and low		—	—	50	mV
V_{OS}	Output voltage offset	(V_{OP} - V_{OM})/2, R_T = 100 Ohm	1.125	1.20	1.395	V
ΔV_{OS}	Change in V_{OS} between H and L		—	—	50	mV
I_{OSD}	Output short circuit current	V_{OD} = 0 V driver outputs shorted	—	—	24	mA

LVDS Emulation

MachXO3L/LF devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)



Note: All resistors are ±1%.

Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	158	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

BLVDS

The MachXO3L/LF family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

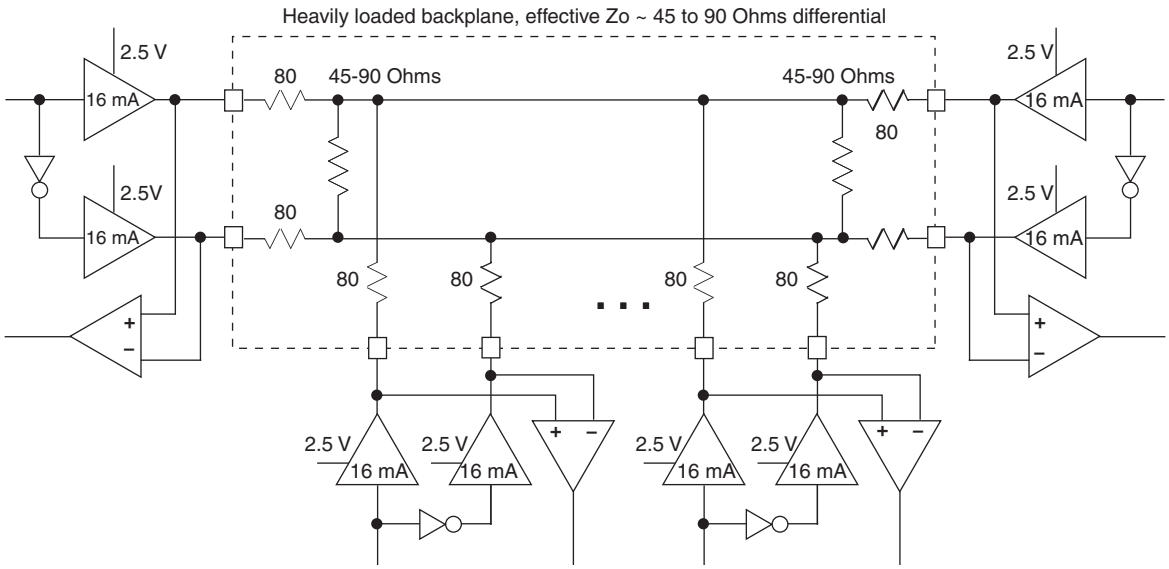


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z_{OUT}	Output impedance	20	20	Ohms
R_S	Driver series resistance	80	80	Ohms
R_{TLEFT}	Left end termination	45	90	Ohms
R_{TRIGHT}	Right end termination	45	90	Ohms
V_{OH}	Output high voltage	1.376	1.480	V
V_{OL}	Output low voltage	1.124	1.020	V
V_{OD}	Output differential voltage	0.253	0.459	V
V_{CM}	Output common mode voltage	1.250	1.250	V
I_{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

Parameter	Description	Device	–6		–5		Units
			Min.	Max.	Min.	Max.	
MIPI D-PHY Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input - GDDRX4_RX.ECLK.Centered[10, 11, 12]							
t_{SU}[15]	Input Data Setup Before ECLK	All MachXO3L/LF devices, bottom side only	0.200	—	0.200	—	UI
t_{HO}[15]	Input Data Hold After ECLK		0.200	—	0.200	—	UI
f_{DATA}[14]	MIPI D-PHY Input Data Speed		—	900	—	900	Mbps
f_{DDRX4}[14]	MIPI D-PHY ECLK Frequency		—	450	—	450	MHz
f_{SCLK}[14]	SCLK Frequency		—	112.5	—	112.5	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[8]							
t_{DIA}	Output Data Invalid After CLK Output	All MachXO3L/LF devices, all sides	—	0.520	—	0.550	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.520	—	0.550	ns
f_{DATA}	DDRX1 Output Data Speed		—	300	—	250	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	150	—	125	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[8]							
t_{DVB}	Output Data Valid Before CLK Output	All MachXO3L/LF devices, all sides	1.210	—	1.510	—	ns
t_{DVA}	Output Data Valid After CLK Output		1.210	—	1.510	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	300	—	250	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	150	—	125	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[8]							
t_{DIA}	Output Data Invalid After CLK Output	MachXO3L/LF devices, top side only	—	0.200	—	0.215	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.200	—	0.215	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	664	—	554	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	332	—	277	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDRX2 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Centered[8, 9]							
t_{DVB}	Output Data Valid Before CLK Output	MachXO3L/LF devices, top side only	0.535	—	0.670	—	ns
t_{DVA}	Output Data Valid After CLK Output		0.535	—	0.670	—	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	664	—	554	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency (minimum limited by PLL)		—	332	—	277	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDRX4 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_TX.ECLK.Aligned[8, 9]							
t_{DIA}	Output Data Invalid After CLK Output	MachXO3L/LF devices, top side only	—	0.200	—	0.215	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.200	—	0.215	ns
f_{DATA}	DDRX4 Serial Output Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz

Parameter	Description	Device	–6		–5		Units
			Min.	Max.	Min.	Max.	
Generic DDRX4 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_TX.ECLK.Centered[8, 9]							
t_{DVB}	Output Data Valid Before CLK Output	MachXO3L/LF devices, top side only	0.455	—	0.570	—	ns
t_{DVA}	Output Data Valid After CLK Output		0.455	—	0.570	—	ns
f_{DATA}	DDRX4 Serial Output Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency (minimum limited by PLL)		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1[8, 9]							
t_{DIB}	Output Data Invalid Before CLK Output	MachXO3L/LF devices, top side only	—	0.160	—	0.180	ns
t_{DIA}	Output Data Invalid After CLK Output		—	0.160	—	0.180	ns
f_{DATA}	DDR71 Serial Output Data Speed		—	756	—	630	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f_{CLKOUT}	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz
MIPI D-PHY Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input - GDDRX4_TX.ECLK.Centered[10, 11, 12]							
t_{DVB}	Output Data Valid Before CLK Output	All MachXO3L/LF devices, top side only	0.200	—	0.200	—	UI
t_{DVA}	Output Data Valid After CLK Output		0.200	—	0.200	—	UI
f_{DATA}[14]	MIPI D-PHY Output Data Speed		—	900	—	900	Mbps
f_{DDRX4}[14]	MIPI D-PHY ECLK Frequency (minimum limited by PLL)		—	450	—	450	MHz
f_{SCLK}[14]	SCLK Frequency		—	112.5	—	112.5	MHz

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
5. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\ ns)/2$.
6. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
7. This number for general purpose usage. Duty cycle tolerance is +/–10%.
8. Duty cycle is +/– 5% for system usage.
9. Performance is calculated with 0.225 UI.
10. Performance is calculated with 0.20 UI.
11. Performance for Industrial devices are only supported with VCC between 1.16 V to 1.24 V.
12. Performance for Industrial devices and –5 devices are not modeled in the Diamond design tool.
13. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
14. Above 800 Mbps is only supported with WLCSP and csfBGA packages
15. Between 800 Mbps to 900 Mbps:
    a. VIDTH exceeds the MIPI D-PHY Input DC Conditions Table 3-4 and can be calculated with the equation tSU or tH = -0.0005*VIDTH + 0.3284
    b. Example calculations
        i. tSU and tHO = 0.28 with VIDTH = 100 mV
        ii. tSU and tHO = 0.25 with VIDTH = 170 mV
        iii. tSU and tHO = 0.20 with VIDTH = 270 mV

NVCM/Flash Download Time[1, 2]

Symbol	Parameter	Device	Typ.	Units
$t_{REFRESH}$	POR to Device I/O Active	LCMXO3L/LF-640	1.9	ms
		LCMXO3L/LF-1300	1.9	ms
		LCMXO3L/LF-1300 256-Ball Package	1.4	ms
		LCMXO3L/LF-2100	1.4	ms
		LCMXO3L/LF-2100 324-Ball Package	2.4	ms
		LCMXO3L/LF-4300	2.4	ms
		LCMXO3L/LF-4300 400-Ball Package	3.8	ms
		LCMXO3L/LF-6900	3.8	ms
		LCMXO3L/LF-9400C	5.2	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.
2. The NVCM/Flash download time is measured starting from the maximum voltage of POR trip point.

	MachXO3L/LF-2100					
	WLCSP49	**CSFBGA121**	**CSFBGA256**	**CSFBGA324**	**CABGA256**	**CABGA324**
General Purpose IO per Bank						
Bank 0	19	24	50	71	50	71
Bank 1	0	26	52	62	52	68
Bank 2	13	26	52	72	52	72
Bank 3	0	7	16	22	16	24
Bank 4	0	7	16	14	16	16
Bank 5	6	10	20	27	20	28
Total General Purpose Single Ended IO	38	100	206	268	206	279
Differential IO per Bank						
Bank 0	10	12	25	36	25	36
Bank 1	0	13	26	30	26	34
Bank 2	6	13	26	36	26	36
Bank 3	0	3	8	10	8	12
Bank 4	0	3	8	6	8	8
Bank 5	3	5	10	13	10	14
Total General Purpose Differential IO	19	49	103	131	103	140
Dual Function IO	25	33	33	37	33	37
Number 7:1 or 8:1 Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	7	14	18	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	13	14	18	14	18
High-speed Differential Outputs						
Bank 0	5	7	14	18	14	18
VCCIO Pins						
Bank 0	2	1	4	4	4	4
Bank 1	0	1	3	4	4	4
Bank 2	1	1	4	4	4	4
Bank 3	0	1	2	2	1	2
Bank 4	0	1	2	2	2	2
Bank 5	1	1	2	2	1	2
VCC	2	4	8	8	8	10
GND	4	10	24	16	24	16
NC	0	0	0	13	1	0
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	**49**	**121**	**256**	**324**	**256**	**324**

	MachXO3L/LF-4300						
	WLCSP81	CSFBGA121	CSFBGA256	CSFBGA324	CABGA256	CABGA324	CABGA400
General Purpose IO per Bank							
Bank 0	29	24	50	71	50	71	83
Bank 1	0	26	52	62	52	68	84
Bank 2	20	26	52	72	52	72	84
Bank 3	7	7	16	22	16	24	28
Bank 4	0	7	16	14	16	16	24
Bank 5	7	10	20	27	20	28	32
Total General Purpose Single Ended IO	63	100	206	268	206	279	335
Differential IO per Bank							
Bank 0	15	12	25	36	25	36	42
Bank 1	0	13	26	30	26	34	42
Bank 2	10	13	26	36	26	36	42
Bank 3	3	3	8	10	8	12	14
Bank 4	0	3	8	6	8	8	12
Bank 5	3	5	10	13	10	14	16
Total General Purpose Differential IO	31	49	103	131	103	140	168
Dual Function IO	25	37	37	37	37	37	37
Number 7:1 or 8:1 Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	10	7	18	18	18	18	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	10	13	18	18	18	18	21
High-speed Differential Outputs							
Bank 0	10	7	18	18	18	18	21
VCCIO Pins							
Bank 0	3	1	4	4	4	4	5
Bank 1	0	1	3	4	4	4	5
Bank 2	2	1	4	4	4	4	5
Bank 3	1	1	2	2	1	2	2
Bank 4	0	1	2	2	2	2	2
Bank 5	1	1	2	2	1	2	2
VCC	4	4	8	8	8	10	10
GND	6	10	24	16	24	16	33
NC	0	0	0	13	1	0	0
Reserved for Configuration	1	1	1	1	1	1	1
Total Count of Bonded Pins	**81**	**121**	**256**	**324**	**256**	**324**	**400**

MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-640E-5MG121C	640	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-6MG121C	640	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-5MG121I	640	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-640E-6MG121I	640	1.2 V	6	Halogen-Free csfBGA	121	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-1300E-5UWG36CTR	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR50	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36ITR	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR50	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5MG121C	1300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-6MG121C	1300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-5MG121I	1300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-6MG121I	1300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-5MG256C	1300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-6MG256C	1300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-5MG256I	1300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300E-6MG256I	1300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300C-5BG256C	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-6BG256C	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-5BG256I	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-1300C-6BG256I	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-2100E-5UWG49CTR	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR50	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49ITR	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR50	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5MG121C	2100	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-6MG121C	2100	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-5MG121I	2100	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-6MG121I	2100	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-5MG256C	2100	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-6MG256C	2100	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-5MG256I	2100	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-6MG256I	2100	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-5MG324C	2100	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-6MG324C	2100	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-5MG324I	2100	1.2 V	5	Halogen-Free csfBGA	324	IND

MachXO3 Family Data Sheet Revision History

February 2017 **Advance Data Sheet DS1047**

Date	Version	Section	Change Summary
February 2017	1.8	Architecture	Updated Supported Standards section. Corrected “MDVS” to “MLDVS” in Table 2-11, Supported Input Standards.
		DC and Switching Characteristics	Updated ESD Performance section. Added reference to the MachXO2 Product Family Qualification Summary document.
			Updated Static Supply Current – C/E Devices section. Added footnote 7.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. — Populated values for MachXO3L/LF-9400. — Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, corrected “t_{DVB}” to “t_{DIB}” and “t_{DVA}” to “t_{DIA}” and revised their descriptions. — Added Figure 3-6, Receiver GDDR71_RX Waveforms and Figure 3-7, Transmitter GDDR71_TX Waveforms.
		Pinout Information	Updated the Pin Information Summary section. Added MachXO3L/LF-9600C packages.
May 2016	1.7	DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Modified I/O Tri-state Voltage Applied and Dedicated Input Voltage Applied footnotes.
			Updated sysIO Recommended Operating Conditions section. — Added standards. — Added V_{REF} (V) — Added footnote 4.
			Updated sysIO Single-Ended DC Electrical Characteristics section. Added I/O standards.
		Ordering Information	Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.